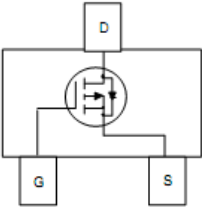
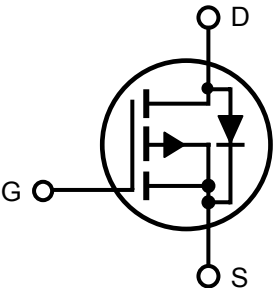
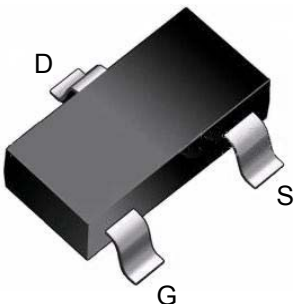


|                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                         |                                                                                                                                          |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------|
| <p>P沟道 增强型 场效应晶体管 片式表面贴封装<br/>P-Channel Enhancement-Mode MOSFETs SMD</p>                                                                                                                                                                                                                                                                                                                                                                                                                                                                | <p><b>HPM2623</b><br/>P-Channel<br/>Enhancement<br/>Mode MOS FETs<br/>对应其他工业型号<br/>2623<br/>Si2623<br/>AP2623<br/>GM2623<br/>CMN2623</p> |
| <p><b>Features</b></p> <ul style="list-style-type: none"> <li>■ -20V, -6A, <math>R_{DS(ON)}=33m\Omega</math> @ <math>V_{GS}=-4.5V</math></li> <li>■ High dense cell design for extremely low <math>R_{DS(ON)}</math></li> <li>■ Rugged and reliable</li> <li>■ Lead free product is acquired</li> <li>■ SOT-23 Package</li> <li>■ Marking Code: 2623</li> </ul> <p>Case Material: Molded Plastic.<br/>UL Flammability Classification Rating 94V-0</p>  |                                                                                                                                          |

|                                                                                                                                     |                                                                                                                               |                                                                                                                                   |
|-------------------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------|
| <p>Internal Block Diagram</p>  <p>SOT-23 内部结构</p> | <p>HPM2623 (SOT-23)</p>  <p>SOT-23 管脚排列</p> | <p>元件标识 (打印)</p>  <p>DEVICE MARKING: 2623</p> |
|-------------------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------|

■ MAXIMUM RATINGS 最大额定值

| Characteristic 特性参数                                                 | Symbol 符号  | Max 最大值     | Unit 单位          |
|---------------------------------------------------------------------|------------|-------------|------------------|
| Drain-Source Voltage 漏极-源极电压                                        | $BV_{DSS}$ | -20         | V                |
| Gate- Source Voltage 栅极-源极电压                                        | $V_{GS}$   | $\pm 10$    |                  |
| Drain Current (continuous) 漏极电流-连续                                  | $I_D$      | -6          | A                |
| Drain Current (pulsed) 漏极电流-脉冲                                      | $I_{DM}$   | -15         |                  |
| Total Device Dissipation 总耗散功率<br>$T_A=25^\circ\text{C}$ (环境温度为25℃) | $P_D$      | 1400        | mW               |
| Junction 结温                                                         | $T_j$      | 150         | $^\circ\text{C}$ |
| Storage Temperature 储存温度                                            | $T_{stg}$  | -55 to +150 |                  |

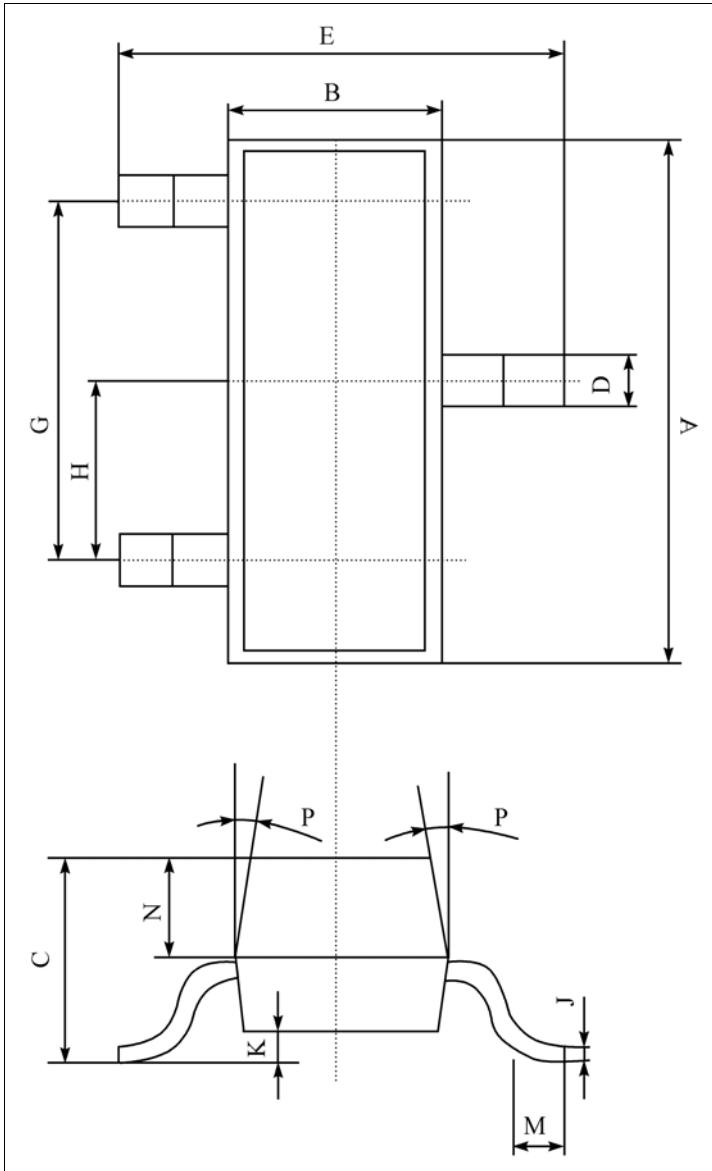
**■ ELECTRICAL CHARACTERISTICS 电特性** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为 $25^{\circ}\text{C}$ )

| Characteristic<br>特性参数                                                                                     |                                            | Symbol<br>符号 | Min<br>最小值 | Typ<br>典型值 | Max<br>最大值 | Unit<br>单位    |
|------------------------------------------------------------------------------------------------------------|--------------------------------------------|--------------|------------|------------|------------|---------------|
| Drain-Source Breakdown Voltage<br>漏极-源极击穿电压 ( $I_D=-250\mu\text{A}$ , $V_{GS}=0\text{V}$ )                 |                                            | $BV_{DSS}$   | -20        | --         | --         | V             |
| Gate Threshold Voltage<br>栅极开启电压 ( $I_D=-250\mu\text{A}$ , $V_{GS}=V_{DS}$ )                               |                                            | $V_{GS(th)}$ | -0.6       | --         | -1.4       |               |
| Diode Forward Voltage Drop<br>内附二极管正向压降 ( $I_S=-1\text{A}$ , $V_{GS}=0\text{V}$ )                          |                                            | $V_{SD}$     | --         | --         | -1.5       |               |
| Zero Gate Voltage Drain Current<br>零栅压漏极电流 ( $V_{GS}=0\text{V}$ , $V_{DS}=-20\text{V}$ )                   |                                            | $I_{DSS}$    | --         | --         | -1         | $\mu\text{A}$ |
| Gate Body Leakage 栅极漏电流<br>( $V_{GS}=\pm 10\text{V}$ , $V_{DS}=0\text{V}$ )                                |                                            | $I_{GSS}$    | --         | --         | $\pm 100$  | nA            |
| Static Drain-Source<br>On-State Resistance<br>静态漏源导通电阻                                                     | $I_D=-6\text{A}$ , $V_{GS}=-4.5\text{V}$   | $R_{DS(ON)}$ | --         | --         | 33         | m $\Omega$    |
|                                                                                                            | $I_D=-2.0\text{A}$ , $V_{GS}=-2.5\text{V}$ |              | --         | --         | 45         |               |
| Input Capacitance 输入电容<br>( $V_{GS}=0\text{V}$ , $V_{DS}=-10\text{V}$ , $f=1\text{MHz}$ )                  |                                            | $C_{ISS}$    | --         | 600        | --         | pF            |
| Common Source Output Capacitance<br>共源输出电容 ( $V_{GS}=0\text{V}$ , $V_{DS}=-10\text{V}$ , $f=1\text{MHz}$ ) |                                            | $C_{OSS}$    | --         | 120        | --         |               |
| Turn-ON Time 开启时间<br>( $V_{DS}=-10\text{V}$ , $I_D=-2.8\text{A}$ , $R_{GEN}=6\Omega$ )                     |                                            | $t_{(on)}$   | --         | 8          | --         | nS            |
| Turn-OFF Time 关断时间<br>( $V_{DS}=-10\text{V}$ , $I_D=-2.8\text{A}$ , $R_{GEN}=6\Omega$ )                    |                                            | $t_{(off)}$  | --         | 60         | --         |               |

Pulse Width  $\leq 300\mu\text{s}$ ; Duty Cycle  $\leq 2.0\%$

■ DIMENSION 外形封装尺寸数据

Package: SOT-23 HAOHAI Package Code: MM



| 序号                                                                                                                                                                    | 数值及公差     |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------|
| A                                                                                                                                                                     | 2.90±0.10 |
| B                                                                                                                                                                     | 1.30±0.10 |
| C                                                                                                                                                                     | 1.00±0.10 |
| D                                                                                                                                                                     | 0.40±0.10 |
| E                                                                                                                                                                     | 2.40±0.20 |
| G                                                                                                                                                                     | 1.90±0.10 |
| H                                                                                                                                                                     | 0.95±0.05 |
| J                                                                                                                                                                     | 0.13±0.05 |
| K                                                                                                                                                                     | 0.00-0.10 |
| M                                                                                                                                                                     | ≥0.20     |
| N                                                                                                                                                                     | 0.60±0.10 |
| P                                                                                                                                                                     | 7±2°      |
| Packing<br>SOT-23 包装规格<br>SMD片式表面贴封装<br>包装方式: 载带卷盘包装<br>Tape & Reel, 3Kpcs/Reel<br>每卷数量3000只 (3Kpcs/Reel)<br>每盒数量30000只 (30Kpcs/BOX)<br>每箱数量300000只 (300Kpcs/Cartons) |           |



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